

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"20040201732"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 16:43
S2	3	(Kasuga-Shigetaka.IN.) and (Matsunaga-Yoshiyuki.IN.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:34
S3	2	(Kasuga-Shigetaka.IN.) and (Inokuma-Kazuyuki.IN.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:18
S4	4	"6366321"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:19
S5	37	"4631400"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:20
S6	1	(Inokuma-Kazuyuki.IN.) and (Matsunaga-Yoshiyuki.IN.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:34
S7	54	(Kasuga-Shigetaka.IN.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 08:59
S8	10	(Kasuga-Shigetaka.IN.) and nMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:37

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S9	1	6844619B2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:37
S10	93	"5345266"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 12:38
S11	8	"6521881"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 13:26
S12	958	(348/308.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 13:27
S13	43	(348/308.ccls.) and (DSP)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 13:30
S14	10	(348/308.ccls.) and (DSP) and (nMOS or (n near Mos))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 13:40
S15	160	(348/230.1.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 13:40
S16	15	(348/230.1.ccls.) and (DSP)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 13:44

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S17	55	(348/294.ccls.) and (DSP)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 14:05
S18	23	(348/296.ccls.) and (DSP)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:38
S19	5	(DSP near chip) and ("348".clas.) and (nMOS or (n near mos))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 14:13
S20	92	(DSP near chip) and (nMOS or (n near mos))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 14:14
S21	131	(DSP near3 chip) and (nMOS or (n near mos))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 15:40
S22	94	(DSP near3 chip) and (nMOS or (n near mos)) and (tim\$4 near5 circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 15:41
S23	94	(DSP near3 chip) and (nMOS or (n near mos)) and (tim\$4 near5 circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 15:54
S24	11	(DSP near3 chip) and (electronic near3 shutter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:08

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S25	3	"6975351"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 11:39
S26	6	"6801251"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:09
S27	8	(US-20010050713-\$ or US-20010040631-\$ or US-20040051800-\$ or US-20050286287-\$).did. or (US-6366321-\$ or US-7129985-\$ or US-6483541-\$ or US-6985181-\$).did.	US-PGPUB; USPAT	OR	ON	2006/12/13 17:22
S28	3	S27 and (nMOS or (n near mos)) and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:32
S29	955	(CMOS near5 transistor) and DSP	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:24
S30	136	(CMOS near5 transistor) and (DSP same ((tim\$4 near4 generat\$4) or (clock)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:26
S31	136	(CMOS near5 transistor) and (DSP same ((tim\$4 near4 generat\$4) or (clock)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:26
S32	23036330	(@ad<="20020917")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:27

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S33	89	S32 and S31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:27
S34	3	S27 and (nMOS or (n near mos))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 17:32
S35	24719	(transistor with oxide with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 11:40
S36	4268	(transistor with oxide with substrate) and (ion with implant\$4 with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 11:41
S37	23036340	(@ad<="20020917")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 11:41
S38	3034	(transistor with oxide with substrate) and (ion with implant\$4 with substrate) and S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 11:43
S39	749	(transistor with oxide with substrate with surface) and (ion with implant\$4 with substrate with surface) and S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 11:53
S40	0	(transistor with oxide with substrate with surface) and (ion with implant\$4 with substrate with surface) and S37 and ("348".clas.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 11:46

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S41	177	(transistor with oxide with substrate with surface) and (ion with implant\$4 with substrate with surface) and S37 and (nmos or (n near mos))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 13:38
S42	27	(transistor with oxide with substrate with surface) and (ion with isolat\$4 with implant\$4 with substrate with surface) and S37 and (nmos or (n near mos))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:30
S43	12	(US-20040051800-\$ or US-20010050713-\$ or US-20010040631-\$ or US-20050286287-\$ or US-20010019155-\$).did. or (US-6366321-\$ or US-7129985-\$ or US-6483541-\$ or US-6985181-\$ or US-6975351-\$ or US-6916714-\$ or US-6632723-\$).did.	US-PGPUB; USPAT	OR	ON	2006/12/14 15:53
S44	6	S43 and (nmos or (n near mos))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 16:23
S45	1	S43 and (electronic near3 shutter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 16:23
S46	392	(electronic near shutter) same (benefit or advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:30
S47	5	(electronic near shutter) same (benefit or advantage) same MOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:31
S48	23	(348/296.ccls.) and (DSP)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:38

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S49	23036340	(@ad<="20020917")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:38
S50	17	S48 and S49	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:38
S51	13	S48 and S49 and (electronic near shutter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:43
S52	543	(horizontal same vertical same transistor same conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 14:08
S53	114	(horizontal same vertical same transistor same conductivity) and (imag\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 14:12
S54	9	(horizontal same vertical same shift same register same transistor same conductivity) and (imag\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 14:23
S55	9	(horizontal same vertical same shift same register same transistor same conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 14:23
S56	402	(horizontal same vertical same scan\$4 same circuit) and (transistor same conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 14:33

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S57	218	(horizontal same vertical same scan\$4 same circuit) and (transistor same conductivity) and (@ad<="20020917")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 14:34
S58	473	(257/232.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 16:56
S59	2	(257/232.ccls.) and (vertical with shift with register with conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 16:57
S60	1	("250".clas.) and (vertical with shift with register with conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/08 16:57
S61	142	(Matsunaga-Yoshiyuki.IN.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 08:59
S62	30	(Inokuma-Kazuyuki.IN.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 09:00
S63	72	(Kasuga-Shigetaka.IN.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 09:00
S64	19	S61 and (vertical same circuit.clm.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 09:01

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S65	1	S61 and (DSP same chip.clm.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 09:01
S66	7	S61 and (signal same processing. clm.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 09:03
S67	13	S62 and (signal same processing. clm.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 09:03
S68	4	S63 and (signal same processing. clm.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/11 09:03